

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2580	(118/725).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/16 18:16
L2	683	1 and (control near2 temperature)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/16 18:16
L3	146	2 and RF	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/16 19:11
L4	29	3 and electrostatic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/16 18:17
L9	99	(PAN-SHING-CHYANG LIN-JING-CHENG LEE-HSIEN-MING HUANG-CHENG-LIN HSIEH-CHING-HUA PENG-CHAO-HSIEN SHUE-SHAU-LIN SHUE-SHAULIN). in.	US-PGPUB; USPAT; USOCR	OR	ON	2005/02/16 18:48
L10	4029	(taiwan adj semiconductor).as.	US-PGPUB; USPAT; USOCR	OR	ON	2005/02/16 18:48
L11	2051	10 and plasma	US-PGPUB; USPAT; USOCR	OR	ON	2005/02/16 18:48
L12	48	11 and (control near2 temperature)	US-PGPUB; USPAT; USOCR	OR	ON	2005/02/16 18:49
L15	510	11 and (RF radio)	US-PGPUB; USPAT; USOCR	OR	ON	2005/02/16 18:49
L17	85	15 and ((wafer substrate workpiece target) near2 (heat\$3))	US-PGPUB; USPAT; USOCR	OR	ON	2005/02/16 18:50
L18	214	9 12 17	US-PGPUB; USPAT; USOCR	OR	ON	2005/02/16 18:51

L19	51	18 and (heat\$3).ti,ab,clm.	US-PGPUB; USPAT; USOCR	OR	ON	2005/02/16 18:51
L21	86418	(156/345.\$).CCLS. or ("118").CLAS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/02/16 19:10
L22	384	21 and plasma.ti,ab,clm. and (RF radio) and ((wafer substrate workpiece target) near2 (heat\$3)) and (control near2 temperature)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/16 19:10
L23	334	22 not 3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/16 19:11
L24	332	23 not 19	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/16 19:14